

MOS Memory

Commercial and Military Specifications

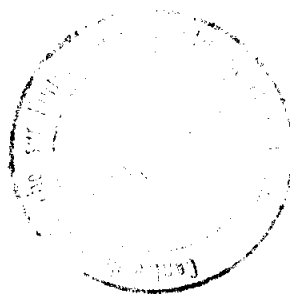
Data Book

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MOS Memory Data Book

Commercial and Military Specifications



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INTRODUCTION

The 1995 *MOS Memory Data Book* from Texas Instruments includes complete detailed specifications on the expanding MOS Memory product line including Dynamic Random Access Memories (DRAMs), Single-In-Line Memory Modules (SIMMs), Erasable Programmable Read-Only Memories (EPROMs), One-Time Programmable Read-Only Memories (OTP PROMs), Electrically Erasable Programmable Read-Only Memories (Flash Memories), and Video RAMs (VRAMs). Also included are military specifications for DRAMs, EPROMs, and VRAMs.

The data book is divided into 12 chapters. Below you will find a brief description of each chapter.

Chapter 1. General Information — Includes an alphanumeric index for quickly finding device numbers and a part number guide with ordering information.

Chapter 2. Selection Guide — An easy-to-use reference guide that includes specific device information. Page numbers are also shown for easy access to the detailed specifications.

Chapter 3. Glossary/Timing Conventions/Data Sheet Structure — Defines terms and standards used throughout the data book.

Chapter 4–8. Product specifications for more than 100 devices can be found in these sections.

Chapter 9. Mechanical Data — Detailed package drawings and specifications are shown in this section.

Chapter 10. Logic Symbols — Includes an explanation and examples of the IEEE standard.

Chapter 11. Quality and Reliability — Details selected processes and the philosophies of Texas Instruments that are used to ensure high quality standards.

Chapter 12. Electrostatic Discharge Guidelines — Because all MOS Memory devices are ESD-sensitive, handling guidelines are included.

For ordering information or further assistance, please contact your nearest Texas Instruments Sales Office or Distributor as listed in the back of this book.

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